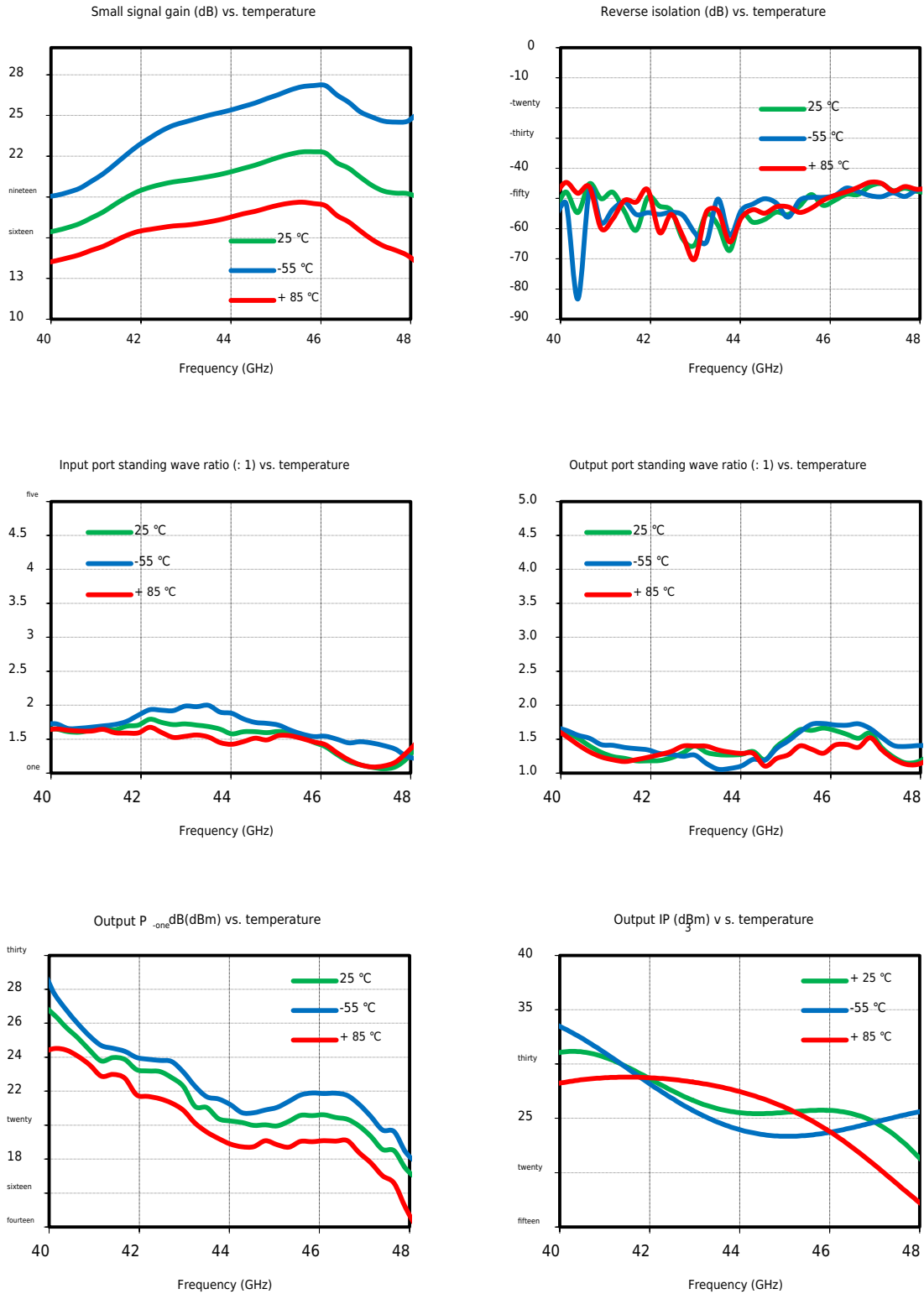


GaAs monolithic integrated driver amplifier

42~47GHz 20dBm

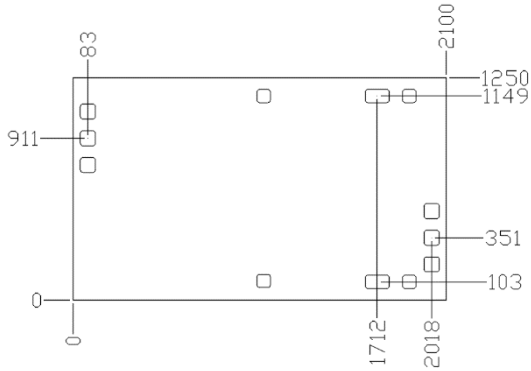
Typical performance curve

$V_D = +5V$ $I_{DQ} = 200mA$, the result obtained by using the AY1512 evaluation board



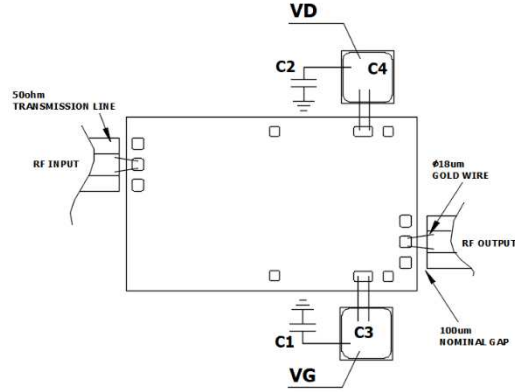
GaAs monolithic integrated driver amplifier
42~47GHz 20dBm

Dimensions (μm)



RFIN, RFOUT pad size:
80x80VG/VD pad size: 140x80

Recommended assembly drawing



Component list

serial number	Numerical value	model	manufacturer	Encapsulation
C1、C2	2.2uF	-	ANY	0603
C3、C4	10pF	-	ANY	SLC

Precautions

1. The chip is stored in a dry, nitrogen environment and used in an ultra-clean environment;
2. GaAs material is brittle and cannot touch the surface of the chip, so you must be careful when using it;
3. Chips are sintered with conductive glue or alloy (the alloy temperature cannot exceed 300°C, and the time cannot exceed 30 seconds) to make it fully grounded;
4. The gap between the microwave port of the chip and the substrate should not exceed 0.1mm. Use Φ18μm double gold wire for bonding. The recommended length of gold wire is 150~250μm;
5. The chip is sensitive to static electricity, so pay attention to anti-static during storage and use;
6. The chip radio frequency input and output and output ports have been integrated into DC blocking capacitors.